

Priority #1

Access DB# 166580

SEARCH REQUEST FORM

Scientific and Technical Information Center

Requester's Full Name: Sin J. Lee Examiner #: 76060 Date: 9-20-2005
 Art Unit: 1752 Phone Number 302-1333 Serial Number: 10/800,195
 Mail Box and Bldg/Room Location: 9266 (Rem.) Results Format Preferred (circle): PAPER DISK E-MAIL

If more than one search is submitted, please prioritize searches in order of need.

 Please provide a detailed statement of the search topic, and describe as specifically as possible the subject matter to be searched. Include the elected species or structures, keywords, synonyms, acronyms, and registry numbers, and combine with the concept or utility of the invention. Define any terms that may have a special meaning. Give examples or relevant citations, authors, etc, if known. Please attach a copy of the cover sheet, pertinent claims, and abstract.

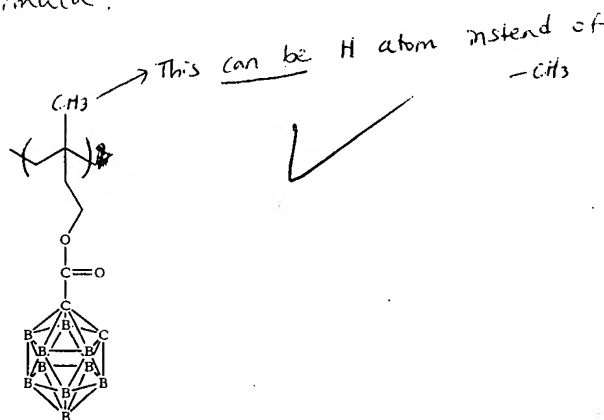
Title of Invention: Plz. See Bib. SCIENTIFIC REFERENCE BR
 Sci & Tech Inf. Cnt.
 Inventors (please provide full names): SEP 2 Rev.

Pat. & T.M. Office
 Earliest Priority Filing Date: _____

For Sequence Searches Only Please include all pertinent information (parent, child, divisional, or issued patent numbers) along with the appropriate serial number.

Plz. search for a resist composition

comprising a boron-containing polymer having the following formula:



STAFF USE ONLY		Type of Search	Vendors and cost where applicable
Searcher: <u>Ros</u>	NA Sequence (#) _____	STN _____	
Searcher Phone #: _____	AA Sequence (#) _____	Dialog _____	
Searcher Location: _____	Structure (#) <u>1</u>	Questel/Orbit _____	
Date Searcher Picked Up: _____	Bibliographic _____	Dr.Link _____	
Date Completed: <u>9/28/05</u>	Litigation _____	Lexis/Nexis _____	
Searcher Prep & Review Time: <u>30</u>	Fulltext _____	Sequence Systems _____	
Clerical Prep Time: _____	Patent Family _____	WWW/Internet _____	
Online Time: <u>94</u>	Other _____	Other (specify) _____	

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FILE 'LREGISTRY' ENTERED AT 10:05:35 ON 28 SEP 2005

L1	STRUCTURE
L2	STRUCTURE
L3	STRUCTURE

FILE 'REGISTRY' ENTERED AT 11:19:22 ON 28 SEP 2005

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        D SCAN
        D SAV
L5      4 SEA SSS FUL L3
        SAV L5 LEE195/A
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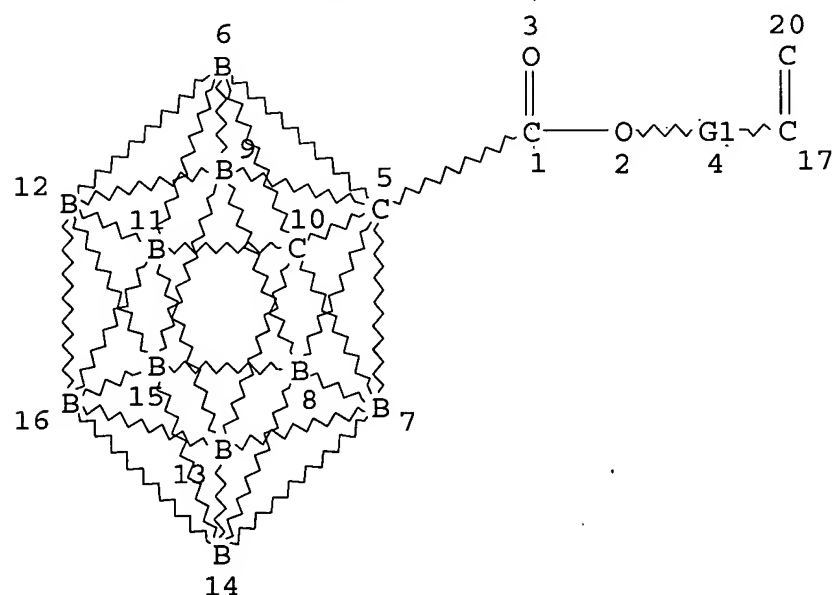
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L6 2 SEA ABB=ON PLU=ON L5

FILE 'REGISTRY' ENTERED AT 11:31:07 ON 28 SEP 2005

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L3 STR



REP G1=(0-5) C
NODE ATTRIBUTES:

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DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:
RING(S) ARE ISOLATED OR EMBEDDED
NUMBER OF NODES IS 18

STEREO ATTRIBUTES: NONE

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L6 ANSWER 1 OF 2 HCAPLUS COPYRIGHT 2005 ACS on STN
2004:230711 Document No. 141:251316 New strategies for lithography at
short wavelengths. Ober, Christopher K.; Kwark, Young-Je;
Bravo-Vasquez, J.-Pablo; Dai, Junyan; Hamad, Alyssandrea (Materials
Science and Engineering, Cornell University, Ithaca, NY, USA). PMSE
Preprints, 90, 22 (English) 2004. CODEN: PPMRA9. ISSN: 1550-6703.
Publisher: American Chemical Society.

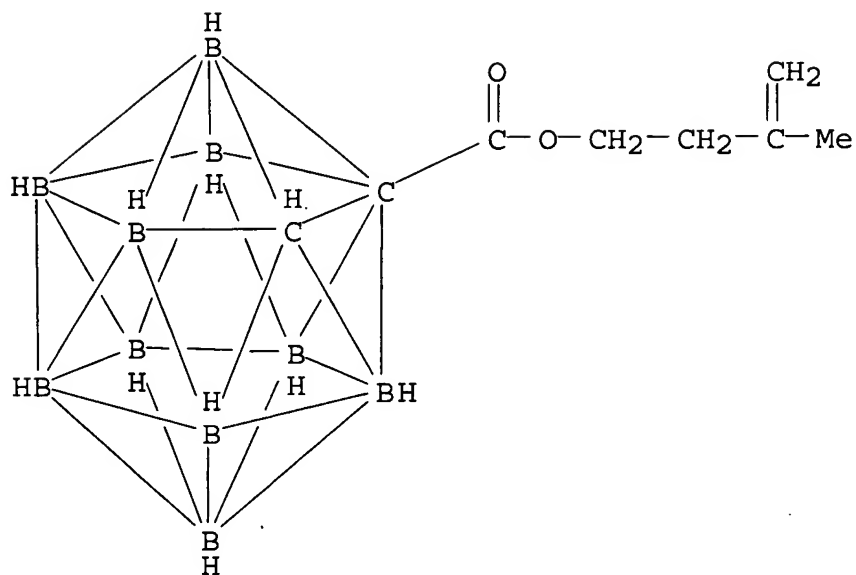
AB New developments are discussed in neg. tone and pos. tone chem.
amplified Si and B-contg. photoresists designed for high resolu. and
high etch resistance. Highly transparent polysilane and
boron-contg. copolymers have shown promising results as resists
materials. Also simple high mol. wt. mols. have been proven
suitable for lithog. and it is expected they will address line-edge
roughness concerns. With the advent of EUV lithog. std. resists
materials will have difficulty fulfilling these new stringent
requirements and we believe our findings provide new insight and
directions in the search for effective EUV resists.

IT 749249-05-6D, derivs.
RL: PRP (Properties); TEM (Technical or engineered material use);
USES (Uses)
(chem. amplified Si and B-contg. photoresists for high resolu.
and high etch resistance)

RN 749249-05-6 HCAPLUS
CN 1,2-Dicarbadoecaborane(12)-1-carboxylic acid, 3-methyl-3-butenyl
ester, polymer with ethenylbenzene and 2-methyl-3-buten-1-ol (9CI)
(CA INDEX NAME)

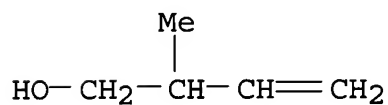
CM 1

CRN 749249-04-5
CMF C8 H20 B10 O2



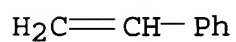
CM 2

CRN 4516-90-9
CMF C5 H10 O



CM 3

CRN 100-42-5
CMF C8 H8



CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
IT 749249-01-2D, derivs. 749249-03-4D, derivs. 749249-05-6D

, derivs. 749249-06-7

RL: PRP (Properties); TEM (Technical or engineered material use);
USES (Uses)

(chem. amplified Si and B-contg. photoresists for high resolu.
and high etch resistance)

L6 ANSWER 2 OF 2 HCAPLUS COPYRIGHT 2005 ACS on STN

1990:532254 Document No. 113:132254 Comparison of three methods for
the synthesis of carboranecarboxylic acid esters. Kahl, Stephen B.
(Dep. Pharm. Chem., Univ. California, San Francisco, CA, 94143-0446,
USA). Tetrahedron Letters, 31(11), 1517-20 (English) 1990. CODEN:
TELEAY. ISSN: 0040-4039. OTHER SOURCES: CASREACT 113:132254.

AB Three procedures for the esterification of polyhedral
carboranecarboxylic acids with long chain unsatd. fatty alcs. are
compared with regard to rate of reaction, ease of isolation and
over-all yield. The optimum procedure is based on room temp.
reaction of the acid chloride and alc. in the presence of
4-dimethylaminopyridine in CH₂Cl₂.

IT 129408-91-9P 129408-96-4P

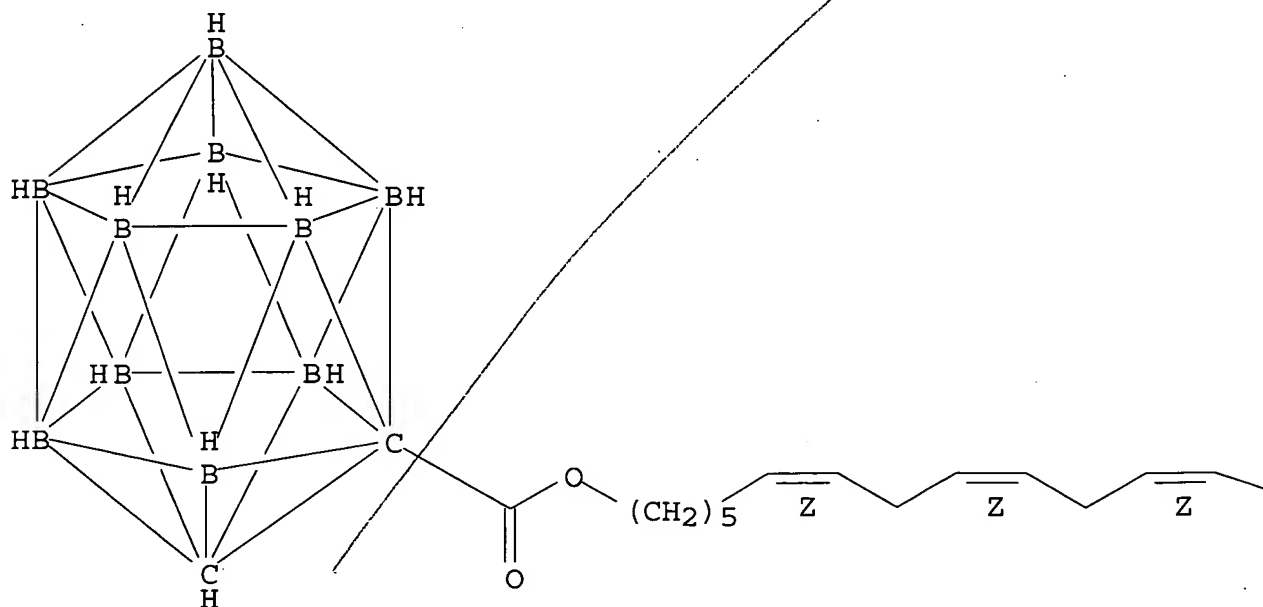
RL: SPN (Synthetic preparation); PREP (Preparation)
(prepn. of)

RN 129408-91-9 HCAPLUS

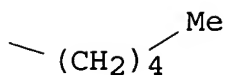
CN 1,2-Dicarbadodecaborane(12)-1-carboxylic acid, 6,9,12-
octadecatrienyl ester, (Z,Z,Z)- (9CI) (CA INDEX NAME)

Double bond geometry as shown.

PAGE 1-A



PAGE 1-B

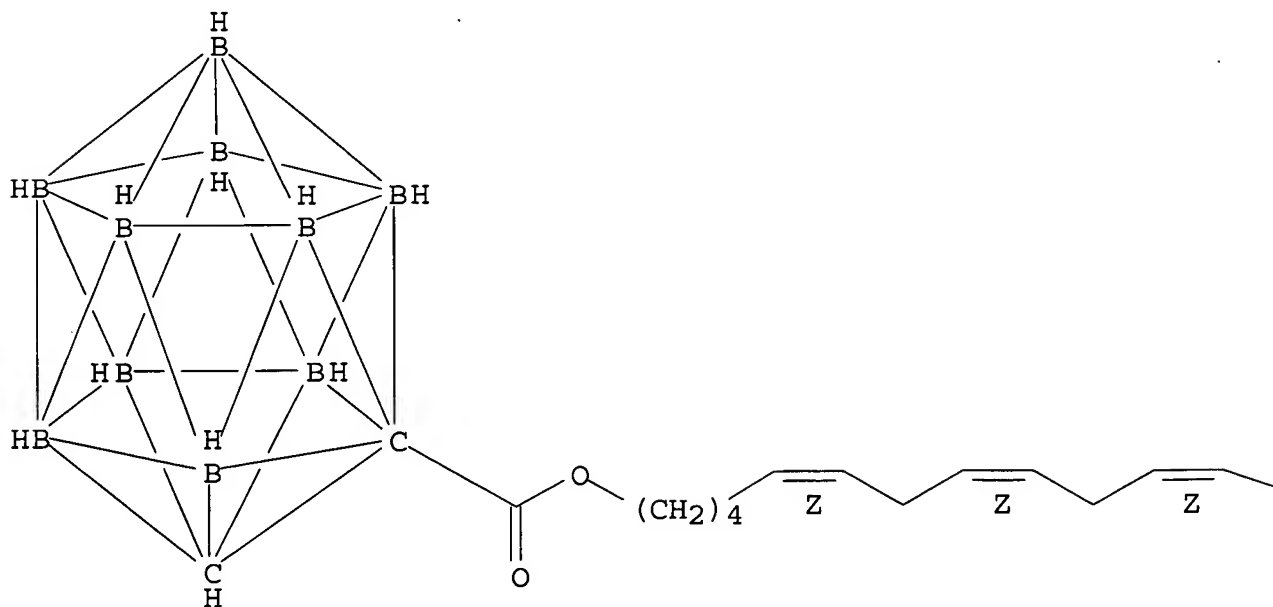


RN 129408-96-4 HCAPLUS

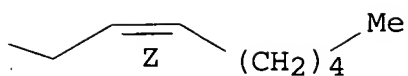
CN 1,2-Dicarbadoecaborane(12)-1-carboxylic acid, 5,8,11,14-eicosatetraenyl ester, (all-Z) - (9CI) (CA INDEX NAME)

Double bond geometry as shown.

PAGE 1-A



PAGE 1-B



CC 29-4 (Organometallic and Organometalloidal Compounds)
 IT 129408-89-5P 129408-90-8P **129408-91-9P** 129408-92-0P
 129408-93-1P 129408-94-2P 129408-95-3P **129408-96-4P**
 129408-97-5P 129408-98-6P
 RL: SPN (Synthetic preparation); PREP (Preparation)
 (prepn. of)

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